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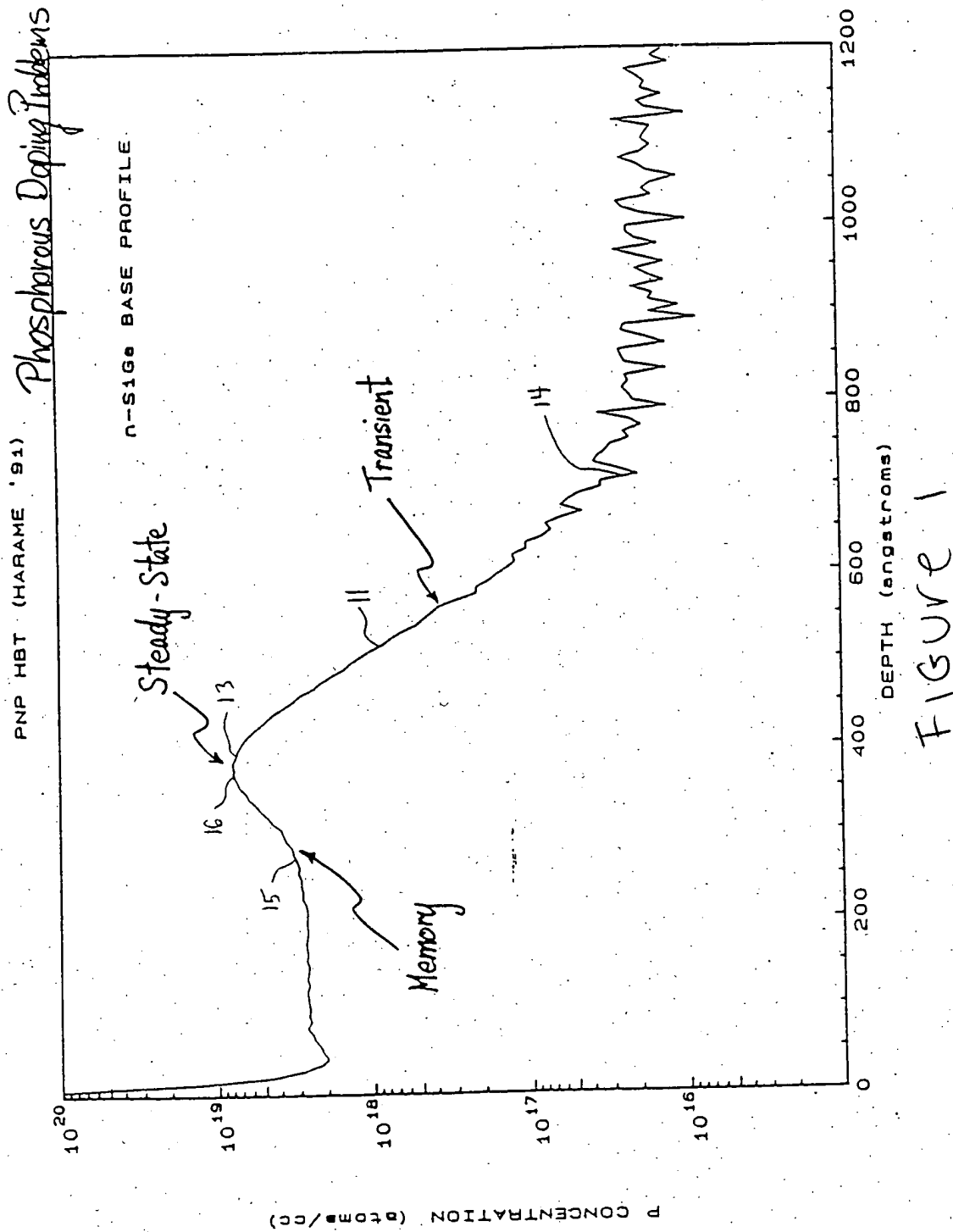


FIGURE 1

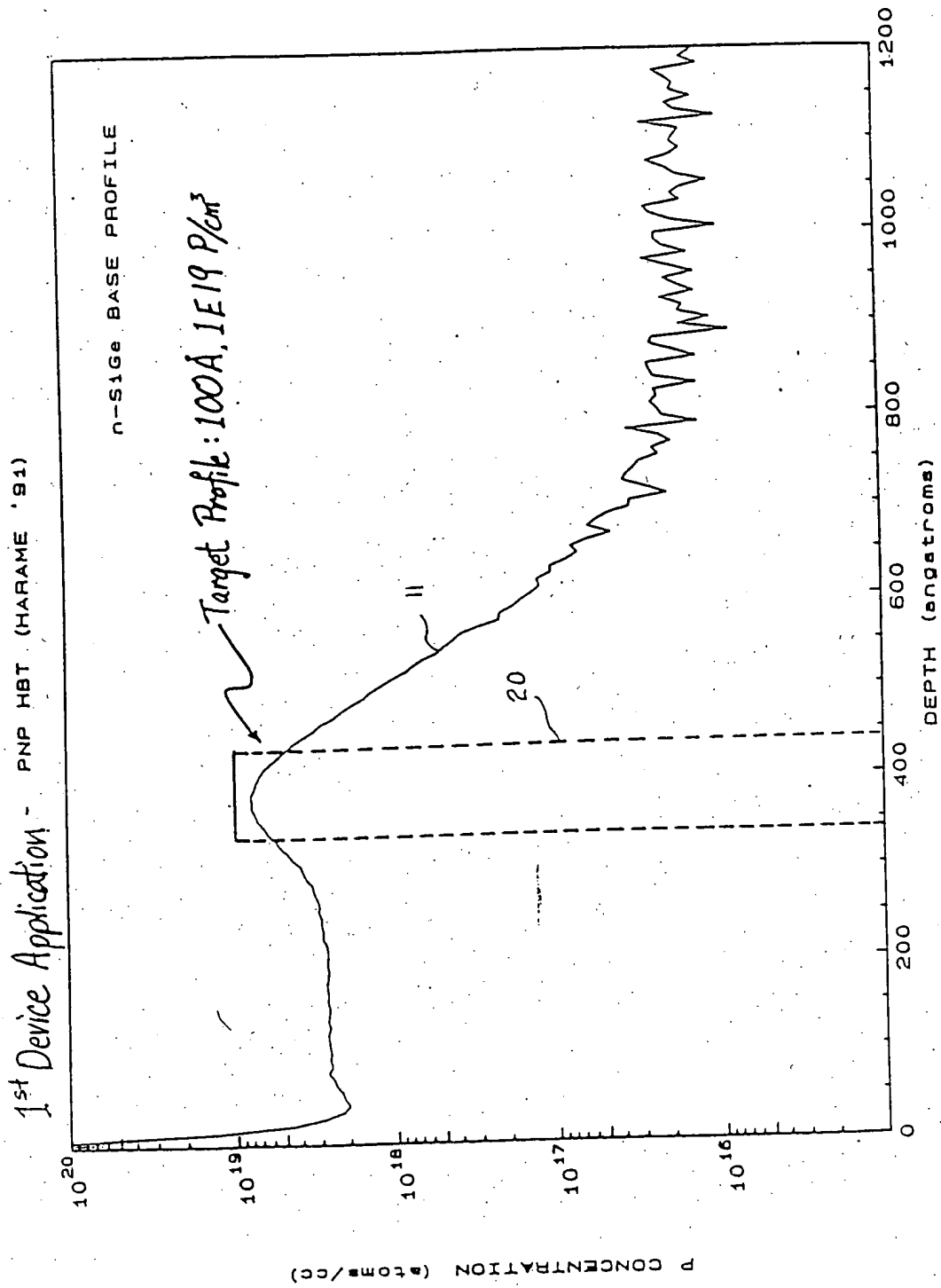


Figure 2

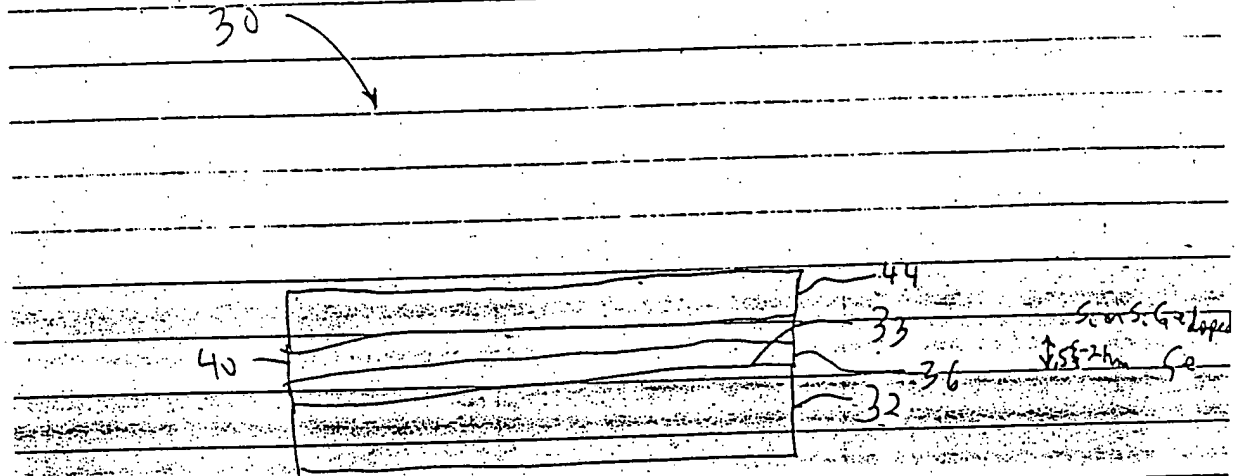


FIGURE 3

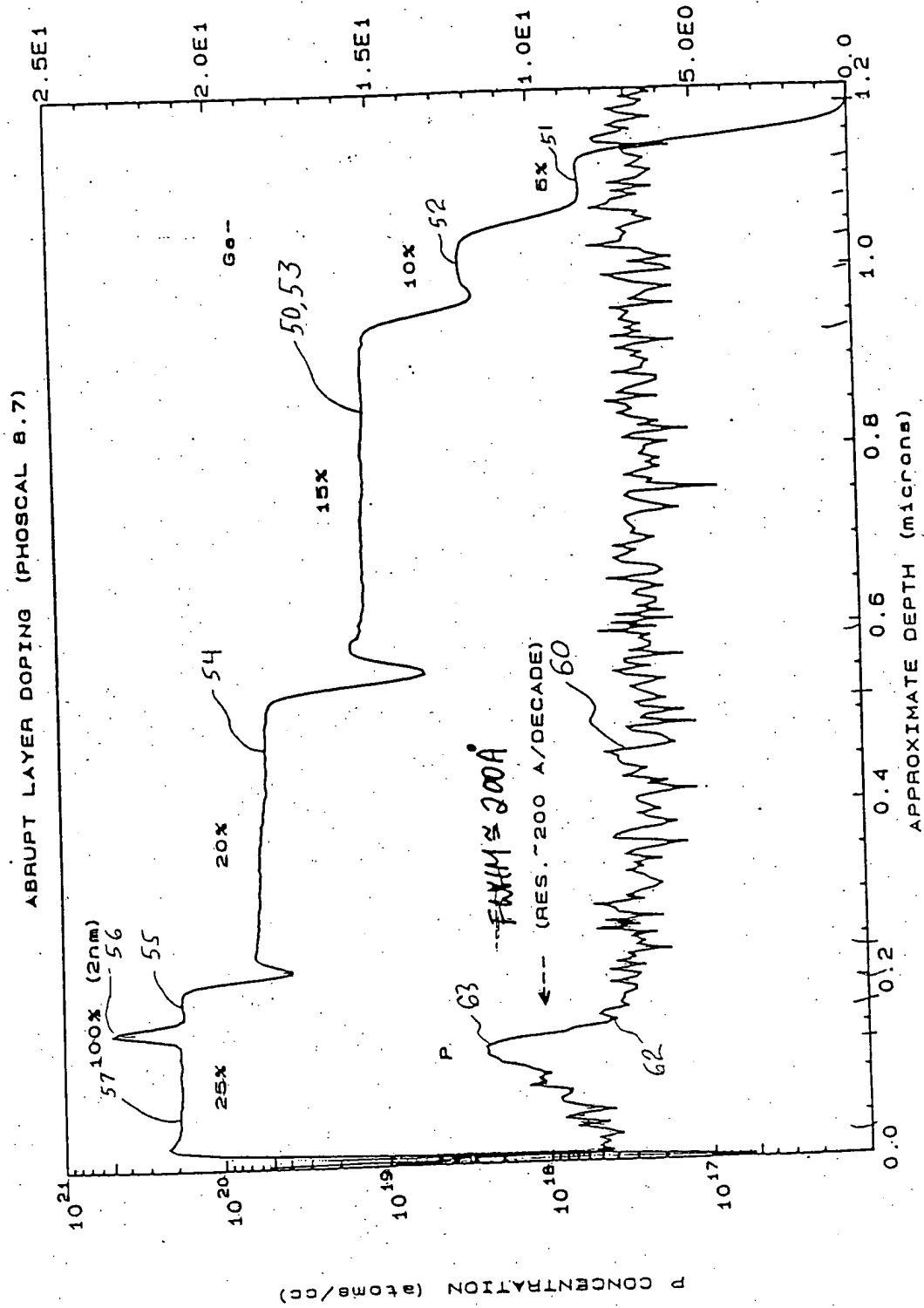
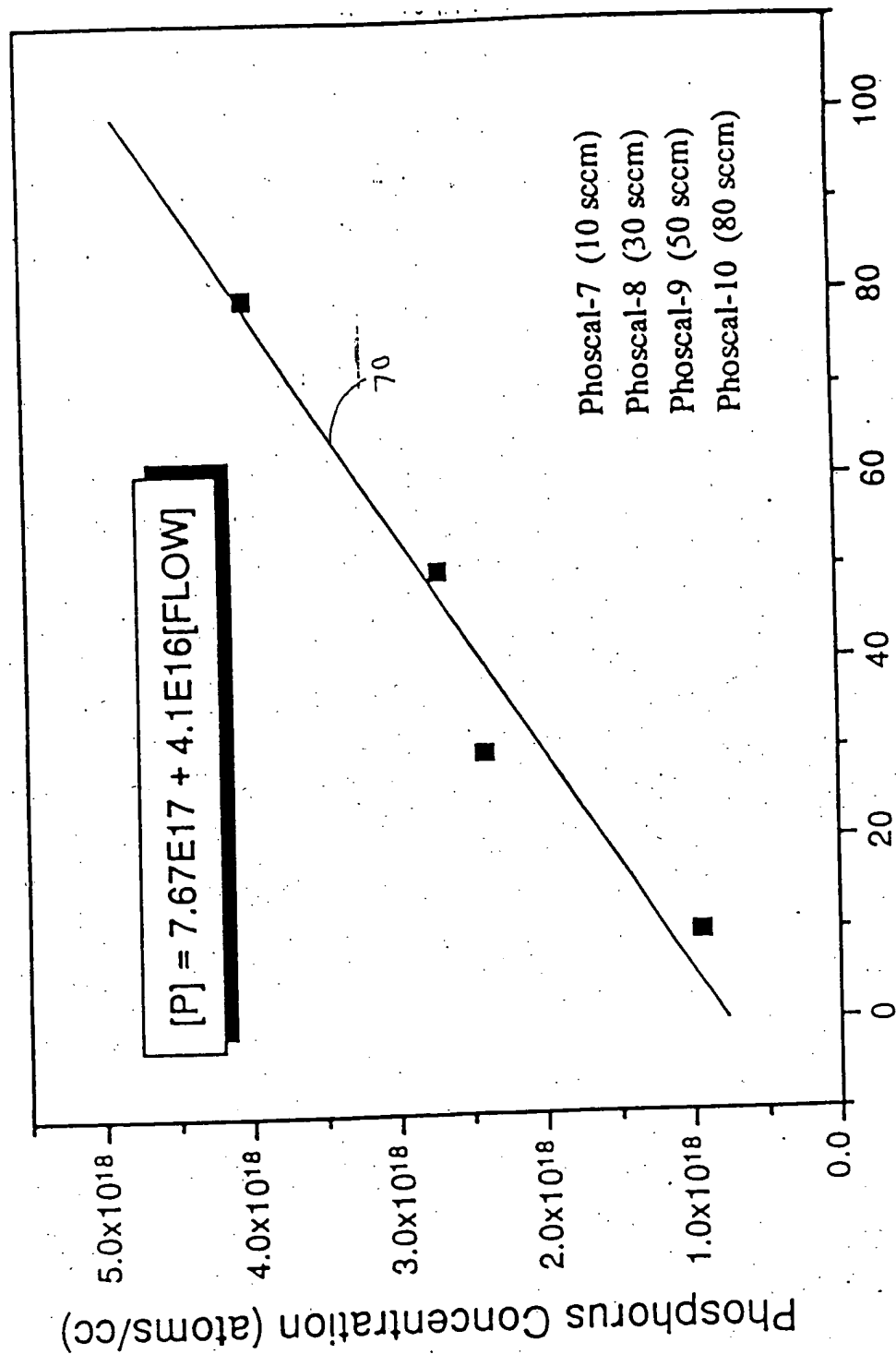


FIGURE 4

# Ge:P Delta Doping Calibration @ 480 C



100 PPM PH<sub>3</sub>/He Mixture Flow (SCCM)

FIGURE 5

## P-doping calibration

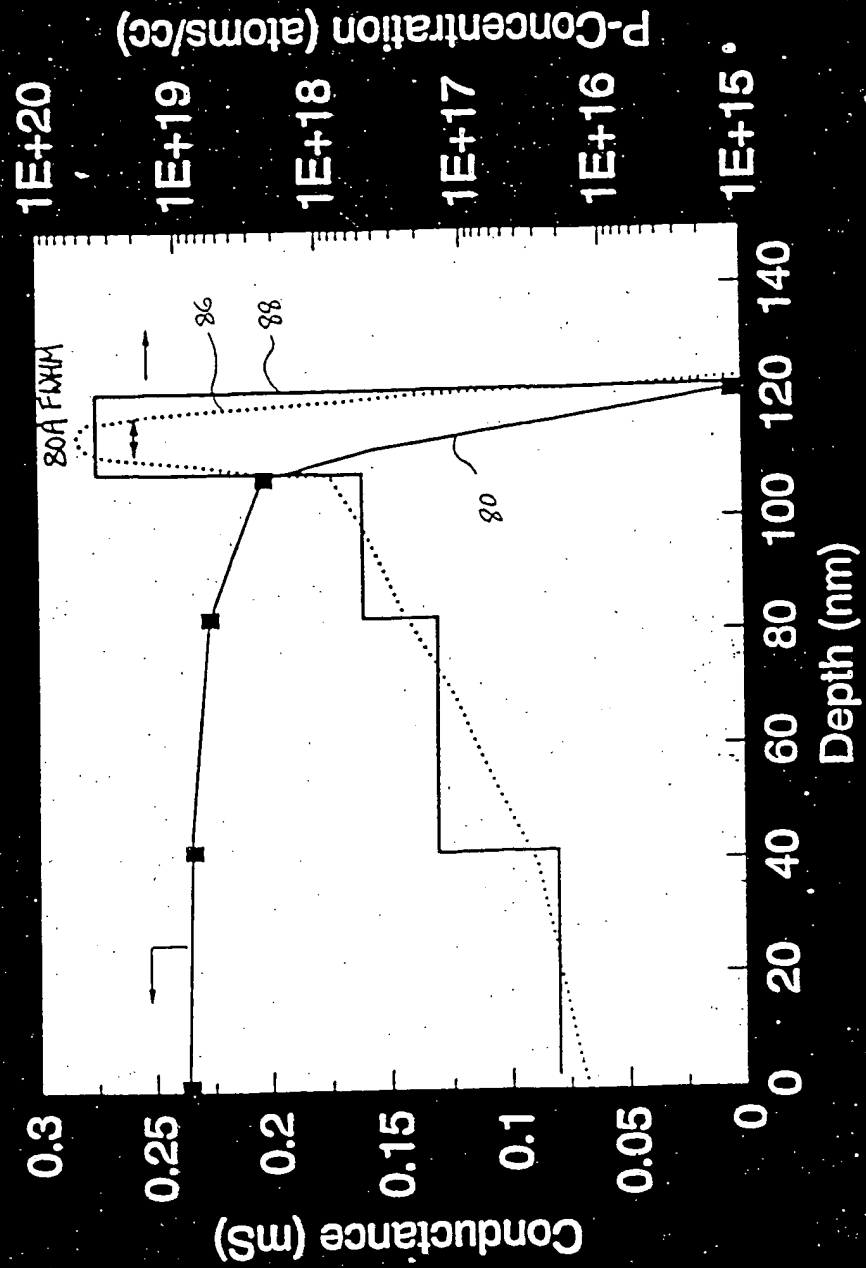


FIGURE 6

# Application of abrupt implantation for channel doping engineering

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implantation, followed by recrystallization

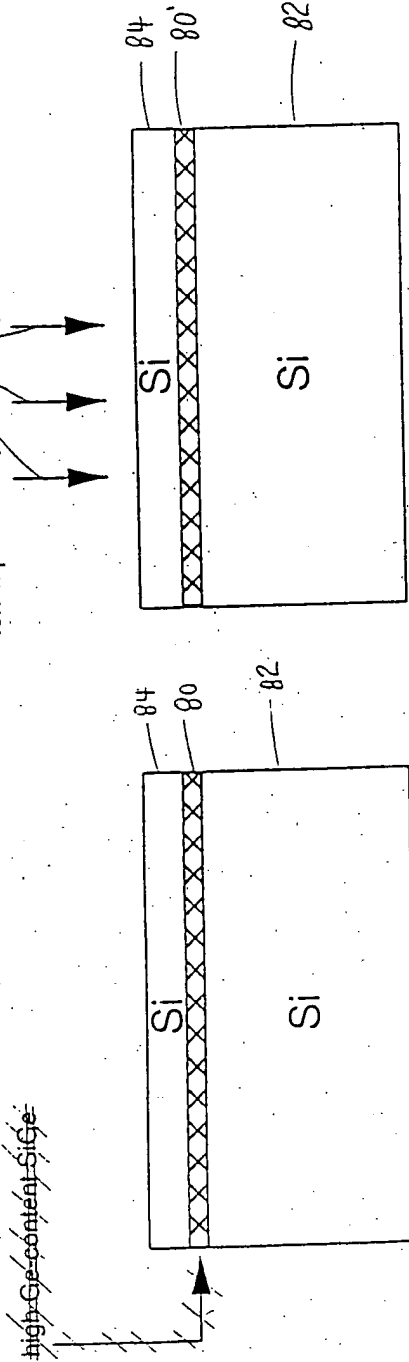


FIGURE 7

FIGURE 8

FIGURE 9

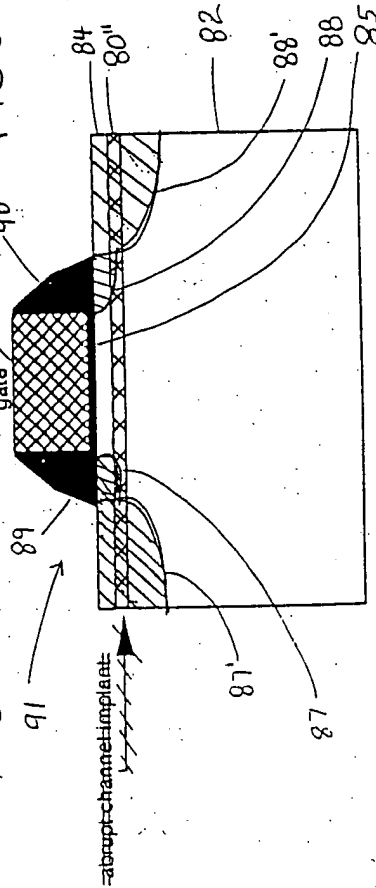


FIGURE 9



# Application of abrupt doping in FET design

